



# PRODUCT/PROCESS CHANGE NOTIFICATION

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PCN MMS-MMY/13/8276  
Dated 27 Dec 2013

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**M93S46, M93S56 & M93S66, MICROWIRE serial EEPROM with  
block protection Industrial grade Redesign & upgrade to  
the CMOSF8H process technology**

**Table 1. Change Implementation Schedule**

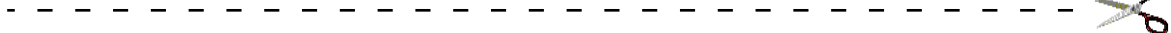
|  |             |
|--|-------------|
| Forecasted implementation date for change  | 20-Dec-2013 |
| Forecasted availability date of samples for customer   | 20-Dec-2013 |
| Forecasted date for <b>STMicroelectronics</b> change Qualification Plan results availability | 31-Jan-2014 |
| Estimated date of changed product first shipment   | 28-Mar-2014 |

**Table 2. Change Identification**

|   |   |
|---|---|
| Product Identification<br>(Product Family/Commercial Product) | M93S46, M93S56, M93S66 Industrial grade                     |
| Type of change  | Waferfab technology change                                  |
| Reason for change   | Line up to state-of-the-art of process                      |
| Description of the change                                     | Redesign and upgrade to the new CMOSF8H process technology. |
| Change Product Identification                                 | Process Technology identifier "K" for CMOSF8H               |
| Manufacturing Location(s)                                     |   |

**Table 3. List of Attachments**

|                            |  |
|----------------------------|--|
| Customer Part numbers list |  |
| Qualification Plan results |  |



|  |            |                     |
|--|------------|---------------------|
| Customer Acknowledgement of Receipt  |            | PCN MMS-MMY/13/8276 |
| Please sign and return to STMicroelectronics Sales Office  |            | Dated 27 Dec 2013   |
| <input type="checkbox"/> Qualification Plan Denied<br><input type="checkbox"/> Qualification Plan Approved<br><br><input type="checkbox"/> Change Denied<br><input type="checkbox"/> Change Approved | Name:      |                     |
|  | Title:     |                     |
|  | Company:   |                     |
|  | Date:      |                     |
|  | Signature: |                     |
| Remark<br>.....<br>.....<br>.....<br>.....<br>.....<br>.....<br>.....<br>.....<br>.....<br>.....<br>.....  |            |                     |

## DOCUMENT APPROVAL

| Name              | Function          |
|-------------------|-------------------|
| Leduc, Hubert     | Marketing Manager |
| Rodrigues, Benoit | Product Manager   |
| Pavano, Rita      | Q.A. Manager      |



## PRODUCT / PROCESS CHANGE NOTIFICATION

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### **M93S46, M93S56 & M93S66, 1-Kbit, 2-Kbit & 4-Kbit MICROWIRE serial access EEPROM with block protection Industrial grade Redesign and upgrade to the CMOSF8H process technology**

#### **What is the change?**

The **M93S46, M93S56 and M93S66**, *1-Kbit, 2-Kbit and 4-Kbit MICROWIRE serial access EEPROM with block protection* product families for industrial grade, currently produced using the CMOSF6SP 36% process technology at ST Ang Mo Kio (Singapore) 6" or at GLOBALFOUNDRIES (Singapore) 8" wafer diffusion plants, have been **redesigned** and will be **upgraded** to the **CMOSF8H** process technology at **ST Rousset** (France) 8" wafer diffusion plant.

This upgraded version in CMOSF8H allows offering:

- Write cycles up to 4 millions
- Data retention up to 200 years

The new M93S46, M93S56 and M93S66 in CMOSF8H version are functionally compatible with the current CMOSF6SP 36% version as per common datasheet rev. 5 – March 2013, attached.

These new M93S46, M93S56 and M93S66 are described in a common datasheet for **M93Sxx** rev. 6.

Concurrent to this change, the new M93S46, M93S56 and M93S66 in CMOSF8H, in SO8N, will be assembled with 0.8 mil Copper wire.

#### **Why?**

The strategy of STMicroelectronics Memory Division is to support our customers on a long-term basis. In line with this commitment, the qualification of the M93S46, M93S56 and M93S66 in the new CMOSF8H process technology will increase the production capacity throughput and consequently improve the service to our customers.

**M93S46, M93S56 & M93S66, 1-Kbit, 2-Kbit & 4-Kbit  
MICROWIRE serial access EEPROM with block protection  
Industrial grade  
Redesign and upgrade to the CMOSF8H process technology**

**When?**

The production of the upgraded new M93S46, M93S56 and M93S66 in CMOSF8H with the new CMOSF8H will ramp up from January 2014 and shipments can start from end of March 2014 onward (or earlier upon customer approval).

**How will the change be qualified?**

The new version of the new M93S46, M93S56 and M93S66 in CMOSF8H will be qualified using the standard ST Microelectronics Corporate Procedures for Quality & Reliability.

**Qualification Plan QPMMY1330** is included inside this document, **Qualification Report QRMMY1330** will be available Week 05 / 2014.

**What is the impact of the change?**


- **Form:** Marking change (see **Device marking** paragraph)
- **Fit:** No change
- **Function:** Change on DC characteristic  $I_{CC1}$  **standby supply current**

## How can the change be seen?

### - BOX LABEL MARKING

On the BOX LABEL MARKING, the difference is visible inside the **Finished Good Part Number**: the **process technology** identifier is "K" for the **upgraded version** in **CMOSF8H**, this identifier being "G" or "S" for the current version in CMOSF6SP 36%.




→ Example for M93S66-WMN6TP

|  |   |   |   |
|--|---|---|---|
| <b>STMicroelectronics</b>  | Manufactured under patents or patents pending |   |   |
|  | Country Of Origin:                            | XXXX  |   |
|  | Pb-free                                       | 2 <sup>nd</sup> Level Interconnect  |   |
|  | MSL: 1  | NOT MOISTURE SENSITIVE  |   |
|  | PBT: 260 °C                                   | Category: e4  | ECOPACK2/ROHS                                     |
|  | <b>TYPE:</b>                                  | <b>M93S66-WMN6TP</b>  |   |
|  |   | <b>M93S66-WMN6TPK</b>   | <b>X X</b>  |
|  | Total Qty:                                    | <b>2500</b>   |   |
|  |   | <b>Process Technology:</b><br>"K" for <b>CMOSF8H</b><br>"G" or "S" for CMOSF6SP 36% | <b>Mask revision and/or Wafer diffusion plant</b> |
|  | <b>Trace Codes</b>                            | PPYWWLLL WX TF  | <b>Assembly and Test &amp; Finishing plants</b>   |
| <b>Marking</b>   | <b>93S66WP</b>                                |   |   |
| <b>Bulk ID</b>   | <b>X0X00XXX0000</b>                           |   |   |
|  |   |   |   |
| Please provide the bulk ID for any inquiry   |   |   |   |

## How can the change be seen?

### - DEVICE MARKING

For the **SO8N** package, the difference is visible inside the trace code (*PYWWT*) where the last digit is “**K**” for the **upgraded version** in **CMOSF8H**, this digit being “**G**”, or “**S**” for current versions.

|  | Upgraded<br>CMOSF8H<br>(ST Rousset)   | Current<br>CMOSF6SP 36%<br>(ST Ang Mo Kio)  | Current<br>CMOSF6SP 36%<br>(GLOBALFOUNDRIES)  |
|--|---|---|---|
| <b>SO8N</b><br>Example:<br>M93S66-WMN6TP |  |  |  |



M93S46, M93S56 & M93S66, 1-Kbit, 2-Kbit & 4-Kbit  
MICROWIRE serial access EEPROM with block protection  
Industrial grade  
Redesign and upgrade to the CMOSF8H process technology

**Appendix A- Product Change Information**

|  |  |
|--|--|
| <b>Product family / Commercial products:</b>   | M93S46, M93S56, M93S66<br>products families / Industrial grade   |
| <b>Customer(s):</b>  | All  |
| <b>Type of change:</b>   | Wafer fab process technology change  |
| <b>Reason for the change:</b>  | Line up to state-of-the-art of process   |
| <b>Description of the change:</b>  | Redesign and upgrade to the new CMOSF8H<br>Process technology.   |
| <b>Forecast date of the change:<br/>(Notification to customer)</b>                     | Week 51 / 2013   |
| <b>Forecast date of<br/><u>Qualification samples</u> availability for customer(s):</b> | Available  |
| <b><u>Qualification Report</u> availability:</b>                                       | The <b>Qualification Plan QPMMY1330</b> is included<br>inside this document.<br><br><b>Qualification Report QRMMY1330</b> will be<br>available Week 05 / 2014. |
| <b>Marking to identify the changed product:</b>  | Process Technology identifier "K" for CMOSF8H.   |
| <b>Description of the qualification program:</b>                                       | Standard ST Microelectronics Corporate<br>Procedures for Quality and Reliability   |
| <b>Product Line(s) and/or Part Number(s):</b>  | See Appendix B   |
| <b>Manufacturing location:</b>   | Rousset 8 inch wafer fab   |
| <b>Estimated date of first shipment:</b>   | Week 13 / 2014   |

M93S46, M93S56 & M93S66, 1-Kbit, 2-Kbit & 4-Kbit  
MICROWIRE serial access EEPROM with block protection  
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**Appendix B: Concerned Commercial Part Numbers:**

| <b>Commercial Part Numbers</b> | <b>Package</b> | <b>Samples availability</b>   |
|--------------------------------|----------------|-------------------------------|
| M93S46-WMN6P                   | SO8N           | (no sample for tube delivery) |
| M93S46-WMN6TP                  | SO8N           | Available                     |
| M93S56-WMN6P                   | SO8N           | (no sample for tube delivery) |
| M93S56-WMN6TP                  | SO8N           | Available                     |
| M93S66-WMN6P                   | SO8N           | (no sample for tube delivery) |
| M93S66-WMN6TP                  | SO8N           | Available                     |

M93S46, M93S56 & M93S66, 1-Kbit, 2-Kbit & 4-Kbit  
MICROWIRE serial access EEPROM with block protection  
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**Appendix C: Qualification Plan:**

**See following pages**

# M93Sxx Redesign and Upgrade to the CMOSF8H process technology

## Qualification Plan QPMMY1330 (1/3)

- The new version of the M93Sxx (xx = 46, 56, 66) in CMOSF8H will be qualified using the standard STMicroelectronics corporate procedures for quality and reliability.
- The CMOSF8H process technology and EEPROM new design core have been qualified for Industrial and Automotive products on 3 lots using the driver product M95640 (refer to qualification report QREE0921).
- The M93Sxx microwire serial access EEPROM products are designed with the same technology and similar architecture as the driver product M95640.

# M93Sxx Redesign and Upgrade to the CMOSF8H process technology

## Qualification Plan QPMMY1330 (2/3)

- M93Sxx devices are derived from M93Cxx by metal mask option (same design core), allowing a qualification by similarity, except for all ESD and Latch-up tests.
- The product vehicles used for the die and package qualifications are presented in *Table 1* and *Table 2* respectively.

**Table 1. Product vehicles used for die qualification**

| Product               | Silicon process technology | Wafer fabrication location | Package description | Assembly plant location         |
|-----------------------|----------------------------|----------------------------|---------------------|---------------------------------|
| M93Sxx                | CMOSF8H                    | ST Rousset 8"              | CDIP8               | Engineering assy <sup>(1)</sup> |
| M93Cxx <sup>(2)</sup> | CMOSF8H                    | ST Rousset 8"              | CDIP8               | Engineering assy <sup>(1)</sup> |

1. CDIP8 is a engineering ceramic package used only for die-oriented reliability trials.
2. M93Sxx are derived from M93Cxx devices by metal mask option (same design core). Die qualification results obtained on M93Cxx are applicable to M93Sxx devices, except for all ESD / Latch-up tests.

**Table 2. Product vehicle used for package qualification**

| Product | Silicon process technology | Wafer fabrication location | Package description | Assembly plant location |
|---------|----------------------------|----------------------------|---------------------|-------------------------|
| M93Cxx  | CMOSF8H                    | ST Rousset 8"              | SO8N                | ST Shenzhen             |

# M93Sxx Redesign and Upgrade to the CMOSF8H process technology Qualification Plan QPMY1330 (3/3)

- The reliability test plan related to the new M93Sxx is presented as follows :

| Test    | Test short description                                      |   |                   |             |          |                       |
|---------|---|---|-------------------|-------------|----------|-----------------------|
|         | Method  | Conditions                                | Sample size / lot | No. of lots | Duration | Acceptance Criteria   |
| ESD HBM | <b>Electrostatic discharge (human body model)</b>           |   |                   |             |          |                       |
|         | AEC-Q100-002<br>JESD22-A114                                 | C = 100 pF, R = 1500 Ohms                 | 27                | 1           | N/A      | PASS<br>4000 V        |
| ESD MM  | <b>Electrostatic discharge (machine model)</b>              |   |                   |             |          |                       |
|         | AEC-Q100-003<br>JESD22-A115                                 | C = 200 pF, R = 0 Ohms                    | 12                | 1           | N/A      | PASS<br>400 V         |
| ESD CDM | <b>Electrostatic discharge (charge device model)</b>        |   |                   |             |          |                       |
|         | AEC-Q100-011<br>JESD22-C101                                 | Field induced charging method             | 18                | 1           | N/A      | PASS<br>1500 V        |
| LU      | <b>Latch-up (current injection and over-voltage stress)</b> |   |                   |             |          |                       |
|         | AEC-Q100-004<br>JESD78B                                     | At maximum operating temperature (150 °C) | 6                 | 1           | N/A      | Class II –<br>Level A |

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| <b>Document Revision History</b> |      |                             |
|----------------------------------|------|-----------------------------|
| Date                             | Rev. | Description of the Revision |
| November 19, 2013                | 1.00 | First draft creation        |
|                                  |      |                             |
|                                  |      |                             |
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| <b>Source Documents &amp; Reference Documents</b> |       |       |
|---|-------|-------|
| Source document Title                             | Rev.: | Date: |
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